# **Complementary Power Transistors**

# **DPAK for Surface Mount Applications**

Designed for general purpose amplifier and low speed switching applications.

### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc
Collector-Base Voltage	V <sub>CB</sub>	70	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current	I <sub>C</sub>	10	Adc
Base Current	I <sub>B</sub>	6	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub> <sup>†</sup>	20 0.16	W W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

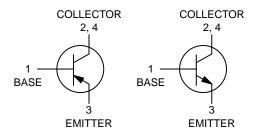


# ON Semiconductor®

http://onsemi.com

# SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

### COMPLEMENTARY





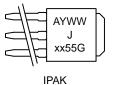


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

### **MARKING DIAGRAMS**





DPAK

A = Assembly Location

Y = Year WW = Work Week Jxx55 = Device Code x = 29 or 30

G = Pb-Free Package

# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

<sup>†</sup>Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	*		1	4
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	60	_	Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	I <sub>CEO</sub>	_	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	I <sub>CEX</sub>	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	Ісво	- -	0.02 2	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 4 Vdc) (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4 Vdc)	h <sub>FE</sub>	20 5	100	-
Collector–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 4 Adc, I <sub>B</sub> = 0.4 Adc) (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 3.3 Adc)	V <sub>CE(sat)</sub>	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 4 Vdc)	V <sub>BE(on)</sub>	-	1.8	Vdc
DYNAMIC CHARACTERISTICS	·			
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f = 500 kHz)	f <sub>T</sub>	2	_	MHz
Pulse Test: Pulse Width < 300 us Duty Cycle < 2%	+			

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

# TYPICAL CHARACTERISTICS

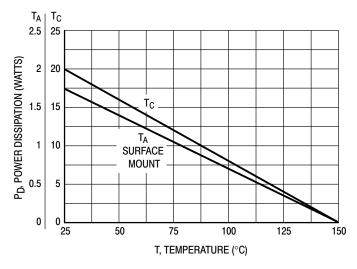


Figure 1. Power Derating

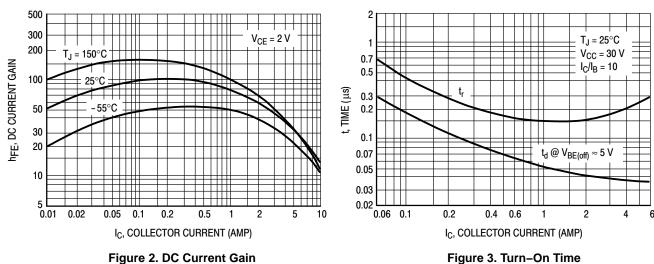


Figure 2. DC Current Gain

1.4

1.2

8.0

0.6

0.4

0.2

0 l

0.1

V, VOLTAGE (VOLTS)

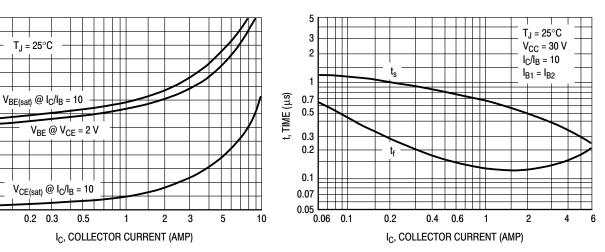


Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

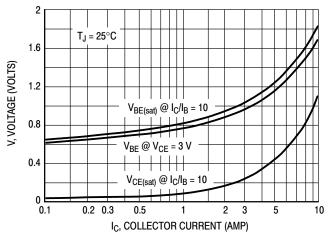
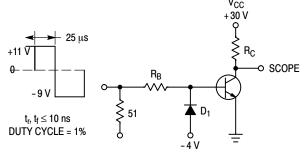


Figure 6. "On" Voltages, MJD2955



 $R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA}$ 

Figure 7. Switching Time Test Circuit

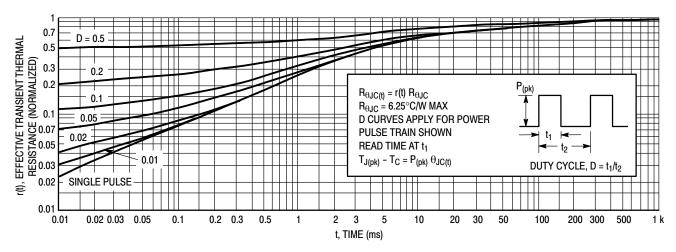


Figure 8. Thermal Response

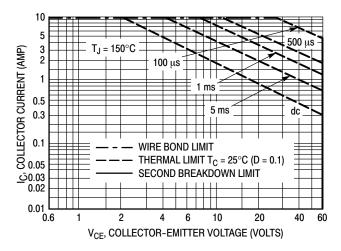


Figure 9. Maximum Forward Bias Safe Operating Area

# Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# **ORDERING INFORMATION**

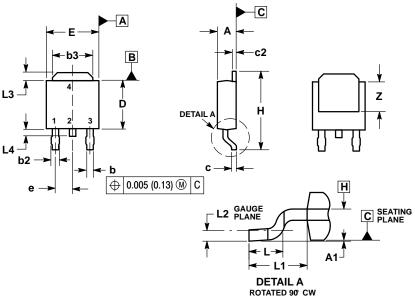
Device	Package Type	Package	Shipping <sup>†</sup>	
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail	
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail	
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel	
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel	
MJD3055G DPAK (Pb-Free)		369C	75 Units / Rail	
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel	
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

# PACKAGE DIMENSIONS

# **DPAK (SINGLE GAUGE)**

CASE 369C ISSUE D



### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: INCHES.

  3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.

  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

  5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.

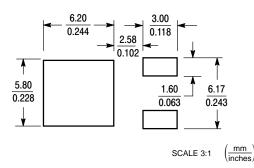
  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIM	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.030	0.045	0.76	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
E	0.250	0.265	6.35	6.73	
е	0.090	BSC	2.29	2.29 BSC	
н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.108 REF		2.74	2.74 REF	
L2	0.020 BSC		0.51	0.51 BSC	
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Z	0.155		3.93		

# STYLE 1: PIN 1. BASE

- 2. COLLECTOR 3. EMITTER 4. COLLECTOR

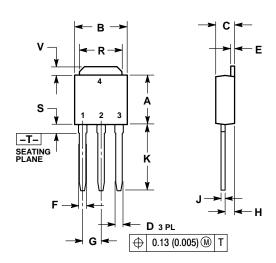
# **SOLDERING FOOTPRINT\***

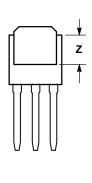


<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

# **IPAK** CASE 369D ISSUE C





- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INIO			ETERO
	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

### STYLE 1:

- PIN 1. BASE
  - 2. COLLECTOR
  - **EMITTER** 3.
  - COLLECTOR

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MJD3055T4 MJD3055T4G MJD2955TF NJVMJD2955T4G NJVMJD3055T4G MJD2955RLG MJD3055RLG